

Title (en)

PRODUCTION OF A TRANSISTOR GATE ON A MULTIBRANCH CHANNEL STRUCTURE AND MEANS FOR ISOLATING THIS GATE FROM THE SOURCE AND DRAIN REGIONS

Title (de)

HERSTELLUNG EINES TRANSISTOR-GATES AUF EINER MEHRZWEIG-KANALSTRUKTUR UND MITTEL ZUM ISOLIEREN DIESES GATES VON DEN SOURCE- UND DRAIN-REGIONEN

Title (fr)

REALISATION SUR UNE STRUCTURE DE CANAL A PLUSIEURS BRANCHES D'UNE GRILLE DE TRANSISTOR ET DE MOYENS POUR ISOLER CETTE GRILLE DES REGIONS DE SOURCE ET DE DRAIN

Publication

EP 1966819 A1 20080910 (FR)

Application

EP 06830845 A 20061228

Priority

- EP 2006070255 W 20061228
- FR 0554151 A 20051230

Abstract (en)

[origin: FR2895835A1] A device has an etched thin-film multilayer comprising two blocks (210, 230) resting on a substrate (200) in which source and drain regions are formed, respectively. Semiconductor bars (220a, 220b) connecting a zone of one block to another zone of another block form a multi-branch transistor channel. A gate surrounding the bars is located between the blocks and is contact with insulating spacers (237a, 237b) in contact with the walls of the blocks. The gate is separated from the blocks by the insulating spacers. An independent claim is also included for forming a microelectronic device.

IPC 8 full level

H01L 21/336 (2006.01); **H01L 29/786** (2006.01)

CPC (source: EP US)

H01L 29/42392 (2013.01 - EP US); **H01L 29/66772** (2013.01 - EP US); **H01L 29/78696** (2013.01 - EP US)

Citation (search report)

See references of WO 2007077194A1

Citation (examination)

- FR 2861501 A1 20050429 - COMMISSARIAT ENERGIE ATOMIQUE [FR]
- US 2003215989 A1 20031120 - KIM SANG-SU [KR], et al

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